

ID200-ID203, ID300-ID301

High-reliability discrete products and engineering services since 1977

SILICON CONTROLLED RECTIFIERS

FEATURES

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• Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.

Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Ratings	Symbol	ID200	ID201	ID202	ID203	ID300	ID301	Unit
Repetitive peak off-state voltage	V _{DRM}	50	100	150	200	300	400	V
Repetitive peak reverse voltage	V _{RRM}	50	100	150	200	300	400	V
Non-repetitive peak reverse voltage (<5ms)	V _{RSM}	75	150	225	300	400	500	V
On-state current								
70°C case	I _{T(RMS)}	1.6					А	
75°C ambient		450						mA
Peak one cycle surge (non-repetitive) on state current	I _{TSM}	15					А	
Repetitive peak on state current	I _{TRM}	Up to 30						А
Rate of rise of on state current	di/dt	100					A/µs	
l ² t (for times > 1.5ms)		0.83					A ² s	
Peak gate current	I _{GM}	250					mA	
Average gate current	I _{G(AV)}	25					mA	
Reverse gate voltage	V_{GR}	6					V	
Storage temperature range	T _{stg}	-65 to 150					°C	
Operating temperature range	TJ	-40 to 110					°C	

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Test	Symbol	Min.	Тур.	Max.	Units	Test Conditions	
Off-state current	I _{DRM}	-	-	10	μΑ	V_{DRM} = rating, R_{GK} = 1K Ω , T = 25°C	
		-	5	100	μΑ	V_{DRM} = rating, R_{GK} = 1K Ω , T = 110°C	
Reverse current	I _{RRM}	-	-	10	μΑ	V_{RRM} = rating, R_{GK} = 1K Ω , T = 25°C	
		-	10	100	μΑ	V_{RRM} = rating, R_{GK} = 1K Ω , T = 110°C	
Gate trigger current	I _{GT}	-	-	200	μΑ	$V_{\rm D}$ = 5V, $R_{\rm GS}$ = 10K Ω , T = 25°C	
		-	-	500	μΑ	$V_{D} = 5V, R_{GS} = 10K\Omega, T = -40^{\circ}C$	
On-state voltage	V _{GT}	0.4	0.52	0.8	V	$V_{D} = 5V, R_{GS} = 100\Omega, T = 25^{\circ}C$	
		0.5	0.7	1.0	V	$V_{D} = 5V, R_{GS} = 100\Omega, T = -40^{\circ}C$	
		0.2	-	-	V	V _D = 5V, R _{GS} = 100Ω, T = 110°C	
Peak on-voltage	V _{TM}	-	-	2.2	V	l _T = 4Amp pulse, T = 25°C	
	I _H	0.3	0.7	3.0	mA	R _{GK} = 1KΩ, T = 25°C	
Holding current		0.4	-	6.0	mA	R _{GK} = 1KΩ, T = -40°C	
		0.2	-	-	mA	R _{GK} = 1KΩ, T = 110°C	
Off-state voltage - critical rate of rise	dv/dt	-	20	-	V/µS	V_{DRM} = Rated, R_{GK} = 1K Ω , T = 110°C	
Turn on time	t _{on}	-	1.0	-	μs	I _G = 10mA, I _T = 1A, V _D = 30V, T = 25°C	
Circuit commutated turn off time	t _q	-	-	40	μs	$I_{T} = I_{R} = 1A, R_{GK} = 1K\Omega, T = 25^{\circ}C$	



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MECHANICAL CHARACTERISTICS

Case	TO-39
Marking	Alpha-numeric
Pin out	See below



		TC	-39		
	Inc	hes	Millimeters		
	Min	Max	Min	Max	
A	0.335	0.370	8.510	9.390	
В	0.305	0.335	7.750	8.500	
С	0.240	0.260	6.100	6.600	
D	0.016	0.021	0.410	0.530	
Ε	0.009	0.041	0.230	1.040	
F	0.016	0.019	0.410	0.480	
G	0.200 BSC		5.080 BSC		
H	0.028	0.034	0.720	0.860	
J	0.029	0.045	0.740	1.140	
K	0.500	0.750	12.700	19.050	
L	0.250	- 19 - 1	6.350	100	
М	45°C BSC		45°C BSC		
Р	177	0.050	121	1.270	
R	0.100	127	2.540	19257	